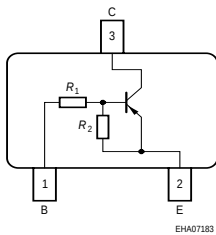
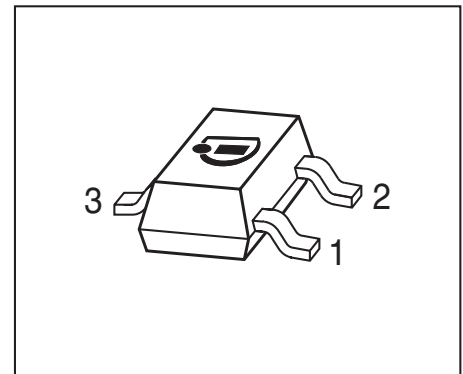


PNP Silicon Digital Transistor

- Built in bias resistor ($R_1 = 2.2 \text{ k}\Omega$, $R_2 = 10 \text{ k}\Omega$)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration			Package
BCR555	XD5	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	20	
Input reverse voltage	$V_{i(rev)}$	5	
Collector current	I_C	500	mA
Total power dissipation- $T_S \leq 79 \text{ }^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 215	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

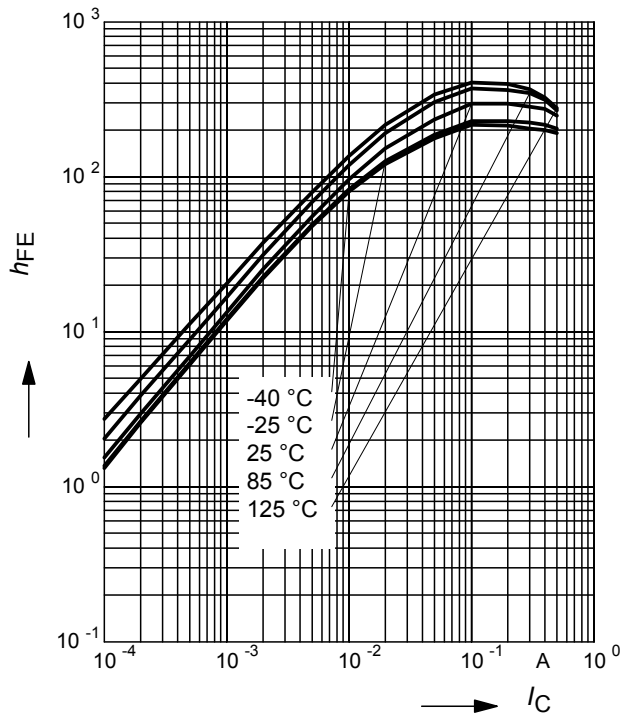
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector-base cutoff current $V_{\text{CB}} = 50\ \text{V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{\text{EB}} = 5\ \text{V}$, $I_C = 0$	I_{EBO}	-	-	0.65	mA
DC current gain- $I_C = 50\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 50\ \text{mA}$, $I_B = 2.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0.4	-	1	
Input on voltage $I_C = 10\ \text{mA}$, $V_{\text{CE}} = 0.3\ \text{V}$	$V_{\text{i(on)}}$	0.5	-	1.4	
Input resistor	R_1	1.5	2.2	2.9	kΩ
Resistor ratio	R_1/R_2	0.19	0.22	0.24	-
AC Characteristics					
Transition frequency $I_C = 50\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_{T}	-	150	-	MHz

¹⁾Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

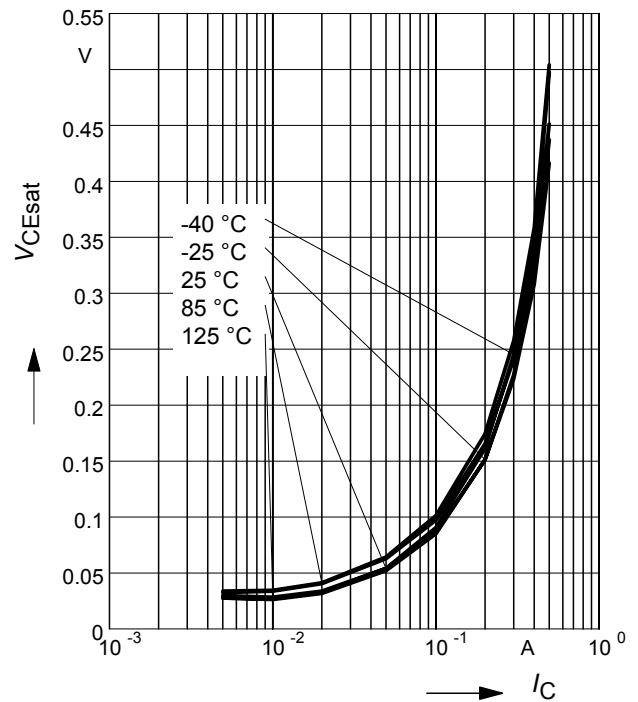
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



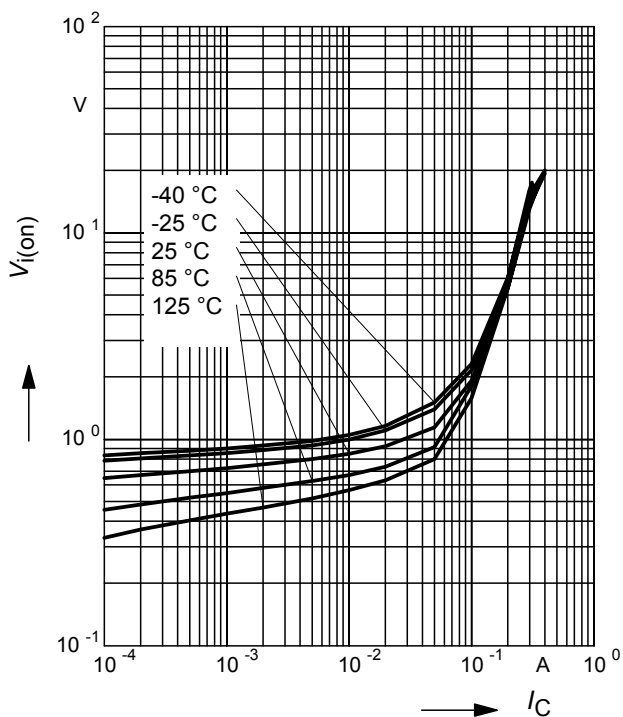
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C)$, $I_C/I_B = 20$



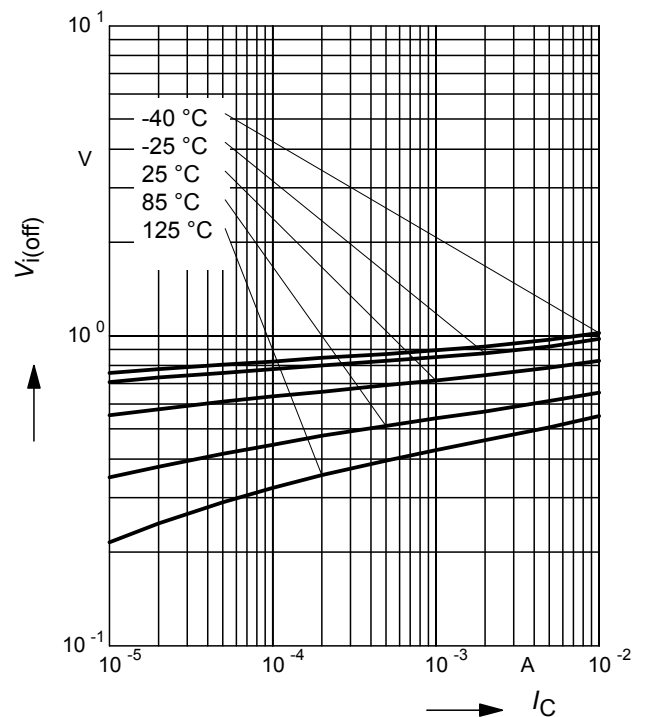
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3 \text{ V}$ (common emitter configuration)

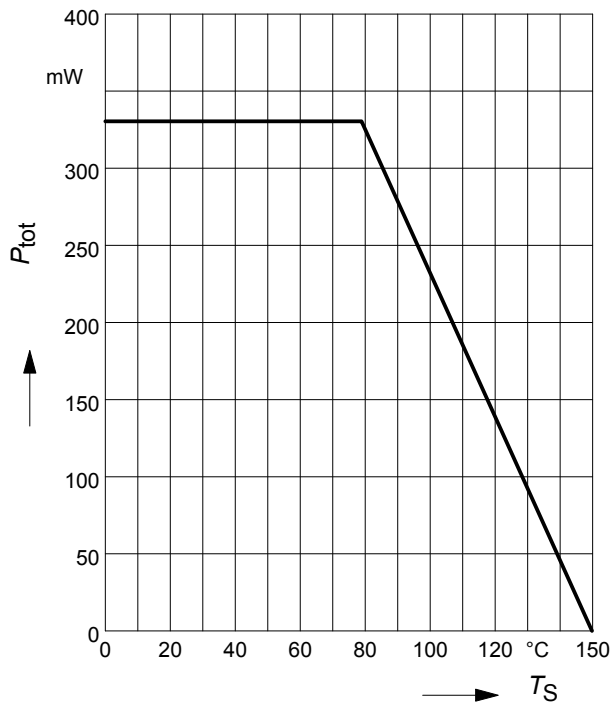


Input off voltage $V_{i(off)} = f(I_C)$

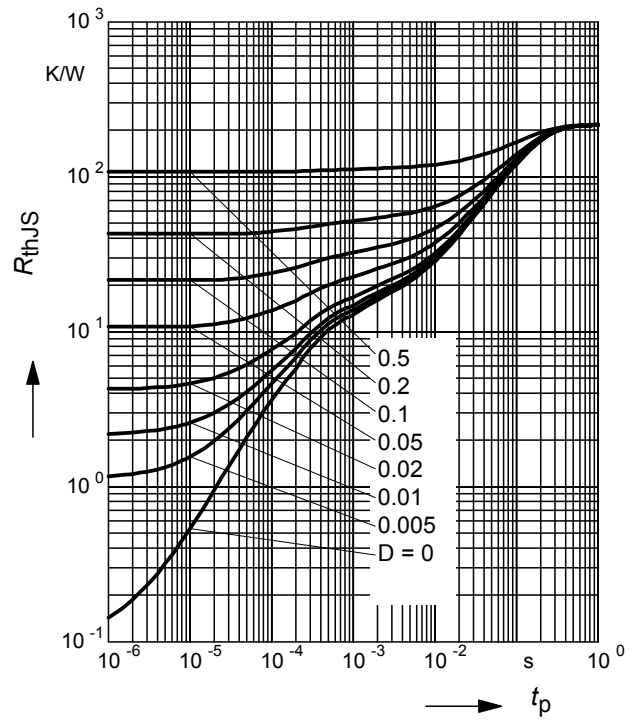
$V_{CE} = 5 \text{ V}$ (common emitter configuration)



Total power dissipation $P_{\text{tot}} = f(T_S)$

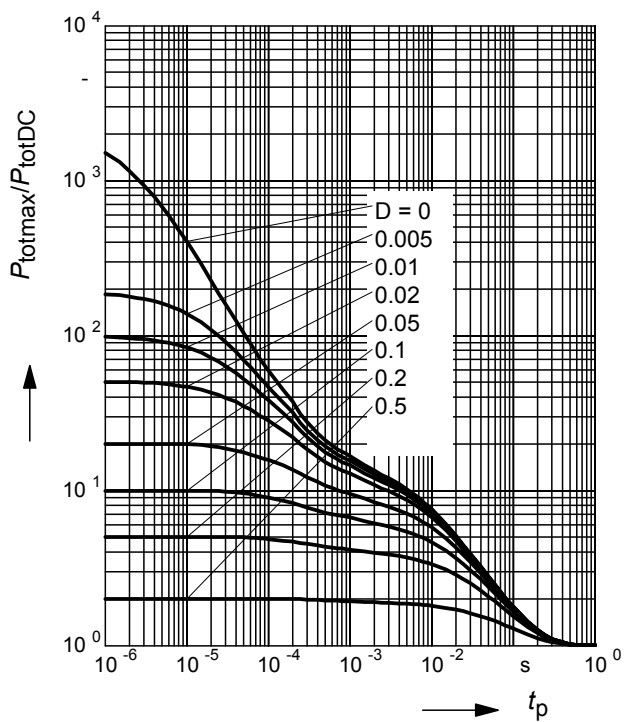


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



Permissible Pulse Load

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$





Technical drawing of a stepped shaft. The drawing shows a shaft with two steps. The top view shows a diameter of 0.8 for the top section and 0.9 for the bottom section. The side view shows a total length of 1.3, with a section of 0.8 for the top step and 0.9 for the bottom section. The bottom view shows a diameter of 0.8 for the left section and 1.2 for the right section. The side view also shows a diameter of 0.9 for the right section.

The diagram shows a top-down view of a BCW66 LED package. It is a rectangular component with four pins. The top pin is labeled 'Pin 1'. The package has a central rectangular area containing the text 'EHS' and '2005, June'. To the right of this area is the Infineon logo. Below the package, the text 'BCW66' and 'Type code' are shown. Lines connect the labels to the corresponding parts of the package: 'Pin 1' to the top pin, 'BCW66' to the bottom of the package, 'Type code' to the bottom of the package, 'Manufacturer' to the Infineon logo, and 'Date code (YM)' to the '2005, June' text.

Pin 1

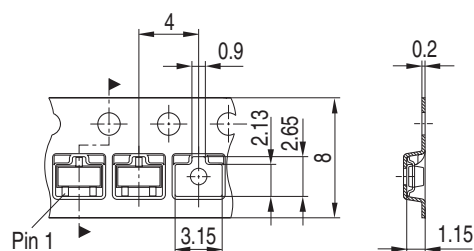
BCW66

Type code

Manufacturer

Date code (YM)

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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